

LET21008

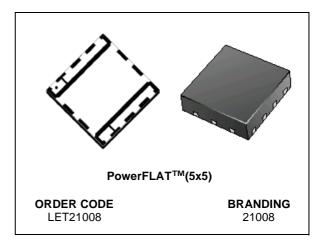
RF POWER TRANSISTORS

Ldmos Enhanced Technology in Plastic Package

TARGET DATA

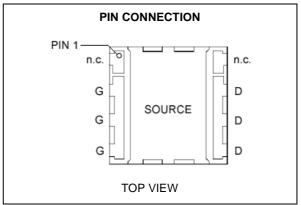
Designed for GSM / EDGE / IS-97 / WCDMA applications

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- P_{OUT} = 8 W with 11 dB gain @ 2170 MHz / 26V
- NEW LEADLESS PLASTIC PACKAGE
- ESD PROTECTION



DESCRIPTION

The LET21008 is a common source N-Channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 26 V in common source mode at frequencies up to 2.1 GHz. LET21008 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the innovative leadless SMD plastic package, PowerFLAT™. LET21008's superior linearity performance makes it an ideal solution for base station applications.



ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25 °C)

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-Source Voltage	65	V
V _{GS}	Gate-Source Voltage	-0.5 to +15	V
I _D	Drain Current	2.0	Α
P _{DISS}	Power Dissipation (@ Tc = 70°C)	TBD	W
Tj	Max. Operating Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

R _{th(j-c)} Junction -Case Thermal Resistance	TBD	°C/W
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April, 15 2003 1/4

ELECTRICAL SPECIFICATION (T_{CASE} = 25 °C)

STATIC

Symbol	Test Conditions				Тур.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0 V	$I_{DS} = 1 \text{ mA}$		65			V
I _{DSS}	V _{GS} = 0 V	V _{DS} = 26 V				1	μΑ
I _{GSS}	V _{GS} = 5 V	V _{DS} = 0 V				1	μΑ
V _{GS(Q)}	V _{DS} = 26 V	I _D = TBD		2.5		5.0	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 1 A			TBD		V
G _{FS}	V _{DS} = 10 V	I _D = 1 A			TBD		mho
C _{ISS}	V _{GS} = 0 V	$V_{DS} = 26 \text{ V}$	f = 1 MHz		TBD		pF
Coss	V _{GS} = 0 V	V _{DS} = 26 V	f = 1 MHz		TBD		pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 26 V	f = 1 MHz		TBD		pF

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
DYNAMIC (f = 21	170 MHz)				
Pour ⁽¹⁾	V _{DD} = 26 V I _{DQ} = TBD	12	15		W
η _D ⁽¹⁾	V _{DD} = 26 V I _{DQ} = TBD	45	50		%
Load mismatch	V _{DD} = 26 V P _{OUT} = 8 W ALL PHASE ANGLES			20:1	VSWR
DYNAMIC (f = 21	110 - 2170 MHz)	•			
Pout ⁽¹⁾	V _{DD} = 26 V I _{DQ} = TBD	8			W
η _D ⁽¹⁾	V _{DD} = 26 V I _{DQ} = TBD	40	45		%
G _P	V _{DD} = 26 V I _{DQ} = TBD P _{OUT} = 8 W	11	13		dB
P _{OUT} (W-CDMA)	ACPR -45 dBc		2.5		W
η _{D(W-CDMA)}	ACPR -45 dBc		25		%

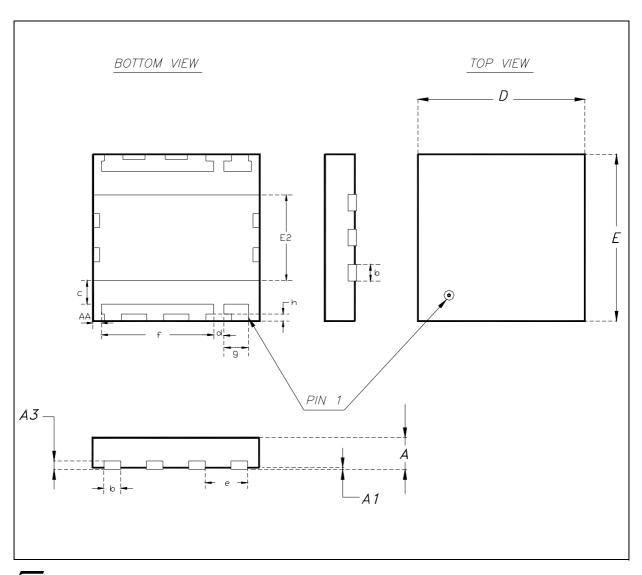
^{(1) 1} dB Compression point

2/4

3/4

PowerFLAT™ MECHANICAL DATA

DIM.		mm			Inch			
Dilvi.	MIN.	TYP.	MAX	MIN.	TYP.	MAX		
Α		0.90	1.00		0.035	0.039		
A1		0.02	0.05		0.001	0.002		
А3		0.24			0.009			
AA	0.15	0.25	0.35	0.006	0.01	0.014		
b	0.43	0.51	0.58	0.017	0.020	0.023		
С	0.64	0.71	0.79	0.025	0.028	0.031		
D		5.00			0.197			
d		0.30			0.011			
Е		5.00			0.197			
E2	2.49	2.57	2.64	0.098	0.101	0.104		
е		1.27			0.050			
f		3.37			0.132			
g		0.74			0.03			
h		0.21			0.008			



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47/